imall

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

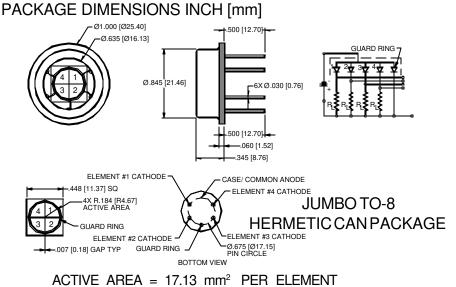
Tel: +86-755-8981 8866 Fax: +86-755-8427 6832 Email & Skype: info@chipsmall.com Web: www.chipsmall.com Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



PHOTONIC DETECTORS INC.

1.06 Micron, High Speed Silicon Photodiode **Quadrant Type PDI-M305**





FEATURES

- .45 A/W @1060 nm
- 12 ns response time
- Low noise

SYMBOL V_{BR}

T_{STG}

To

Ts

 \mathbf{I}_{1}

DESCRIPTION

The **PDI-M305** is a high speed photodiode, processed on high resistivity P type silicon. Guard ring construction for enhanced 1060 nm response and 28 Mhz bandwidth. Packaged in a 6 leaded hermetic TO-5 hermetic package. Ideal for Nd YAG laser.

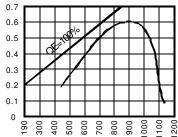
APPLICATIONS

- YAG laser detection
- Navigation
- Tracking and Aligning

ABSOLUTE I

		5 P	EC			
PARAMETER	MIN	MAX	UNITS	(M)	0.7 0.6	
Reverse Voltage		75	V	≺(A	0.5	
Storage Temperature	-55	+125	°C	VIT	0.4 0.3	
Operating Temperature Range	-40	+100	с	ISNO	0.2	4
Soldering Temperature*		+260	°C	SPOI	0.1	
Light Current		500	mA	ЦЦ	190-	300





WAVELENGTH(nm)

*1/16 inch from case for 3 secs max

ELECTRO-OPTICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS			
ع کا	Short Circuit Current	H = 100 fc, 2850 K	375	380		μA			
I _D	Dark Current	H = 0, V _R = 170 V		100	1000	nA			
R _{SH}	Shunt Resistance	$H = 0, V_{R} = 10 \text{ mV}$		-		MΩ			
TC R _{SH}	RSH Temp. Coefficient	$H = 0, V_{R} = 10 \text{ mV}$		-10		% / °C			
CJ	Junction Capacitance	$H = 0, V_{R} = 170 V^{**}$		7	9	рF			
λrange	Spectral Application Range	Spot Scan	400		1150	nm			
λρ	Spectral Response - Peak	Spot Scan		900		nm			
V _{BR}	Breakdown Voltage	I = 1 µµA	250	300		V			
NEP	Noise Equivalent Power	V _R = 10 V @ 900 nm		5x10 ⁻¹¹		W/ V Hz			
tr	Response Time	$RL = 50\Omega V_{R} = 170 V$		12		nS			

Information in this technical data sheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission. Specifications are subject to change without notice. ** f = 1 MHz [FORM NO. 100-PDI-M305 REV N/C]